

30V N-CANNEL ENHANCEMENT MODE MOSFET
Product Summary

BV _{DSS}	Max R _{DS(ON)}	I _D Max T _A = +25°C
30V	460mΩ @ V _{GS} = 4.5V	0.9A
	560mΩ @ V _{GS} = 2.5V	0.83A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

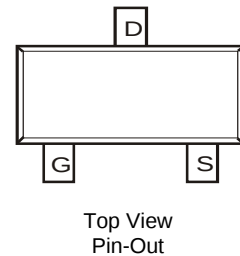
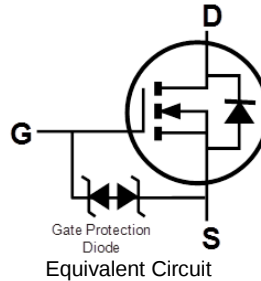
- Load Switch
- Portable Applications
- Power Management Functions

Features and Benefits

- Low V_{GS(TH)}, can be Driven Directly from a Battery
- Low R_{DS(ON)}
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

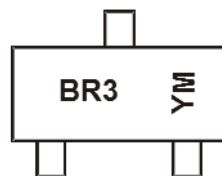
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)


Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Quantity per Reel
DMN3731U-7	BR3	7	3,000
DMN3731U-13	BR3	13	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information


BR3 = Product Type Marking Code
 YM or YM = Date Code Marking
 Y or Y = Year (ex: G = 2019)
 M = Month (ex: 9 = September)

Date Code Key

Date Code Key

Year	2018	2019	2020	2021	2022	2023	2024
Code	F	G	H	I	J	K	L

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = 25°C unless otherwise specified)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	0.9 0.7	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	0.55	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	3	A

Thermal Characteristics

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			P _D	0.4	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		R _{θJA}	303	°C/W
Total Power Dissipation (Note 6)			P _D	0.58	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		R _{θJA}	215	°C/W
Operating and Storage Temperature Range			T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = 25°C unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 10μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	3	μA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.45	—	0.95	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	271	460	mΩ	V _{GS} = 4.5V, I _D = 200mA
			288	560		V _{GS} = 2.5V, I _D = 100mA
			324	730		V _{GS} = 1.8V, I _D = 75mA
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 300mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	—	73	—	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{OSS}	—	7.2	—	pF	
Reverse Transfer Capacitance	C _{RSS}	—	5	—	pF	
Gate Resistance	R _g	—	902	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	—	5.5	—	nC	V _{GS} = 4.5V, V _{DS} = 15V, I _D = 1A
Gate-Source Charge	Q _{gs}	—	0.8	—	nC	
Gate-Drain Charge	Q _{gd}	—	1.4	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	2.5	—	ns	V _{DS} = 10V, I _D = 1A V _{GS} = 10V, R _g = 6Ω
Turn-On Rise Time	t _r	—	3.1	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	477	—	ns	
Turn-Off Fall Time	t _f	—	123	—	ns	I _F = 1A, di/dt = 100A/μs
Reverse Recovery Time	t _{RR}	—	59	—	ns	
Reverse Recovery Charge	Q _{RR}	—	25	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

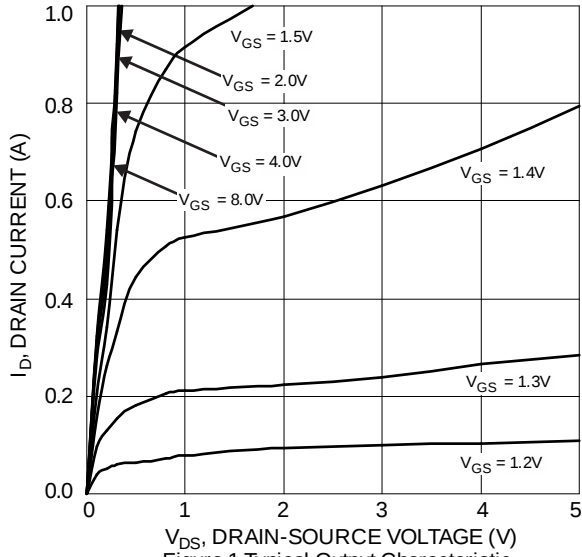


Figure 1 Typical Output Characteristic

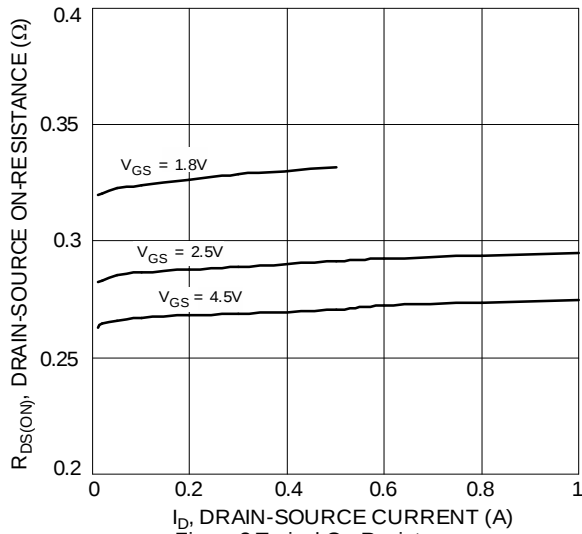


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

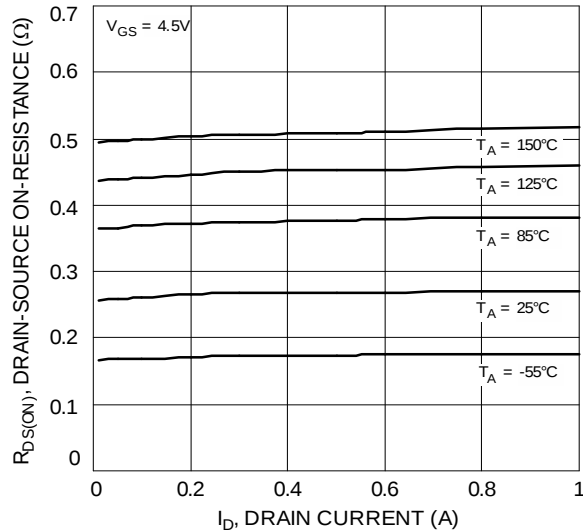


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

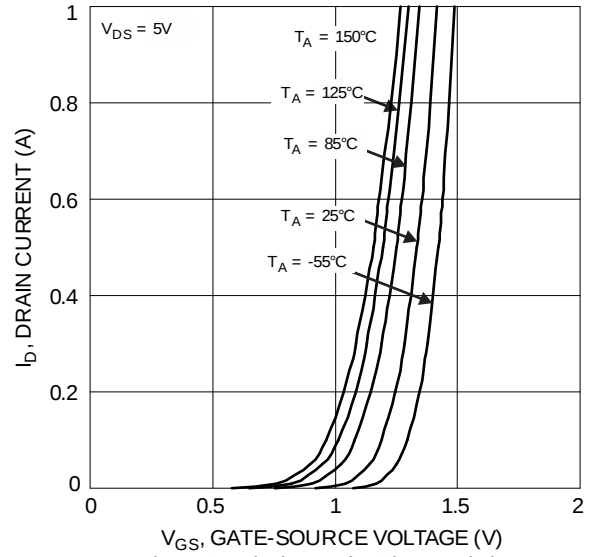


Figure 2 Typical Transfer Characteristics

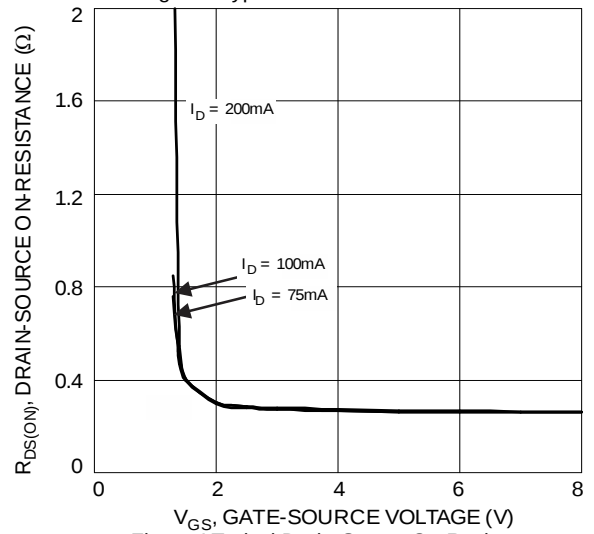


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

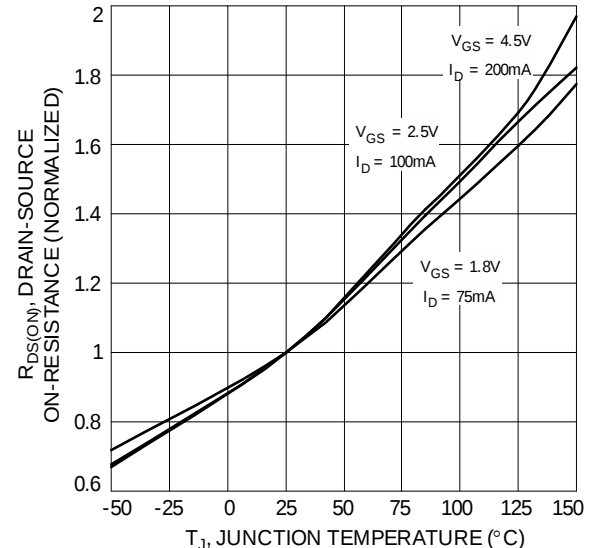


Figure 6 On-Resistance Variation with Temperature

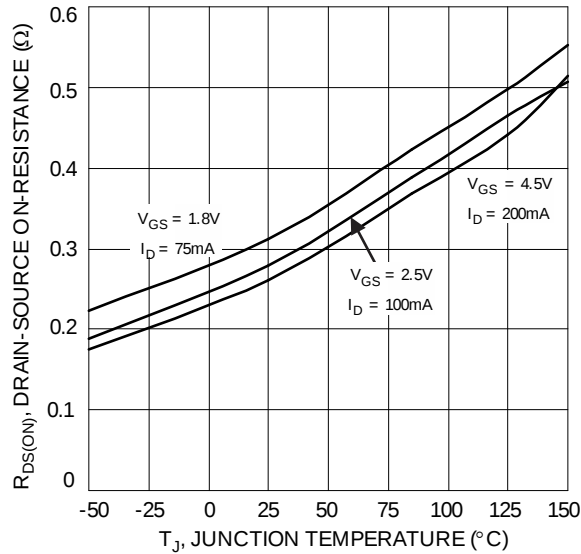


Figure 7 On-Resistance Variation with Temperature

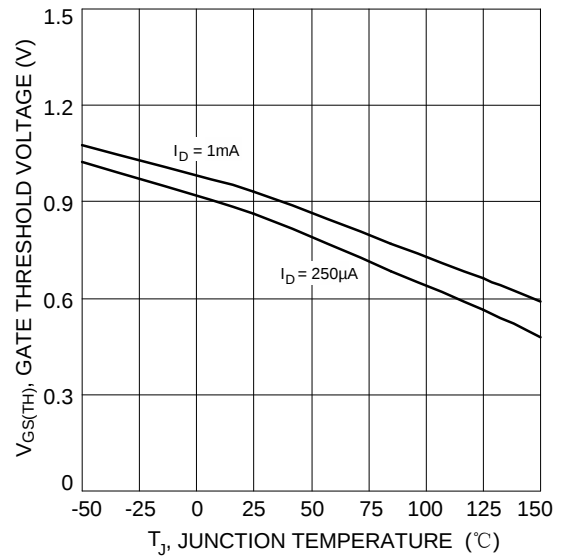


Figure 8 Gate Threshold Variation vs. Junction Temperature

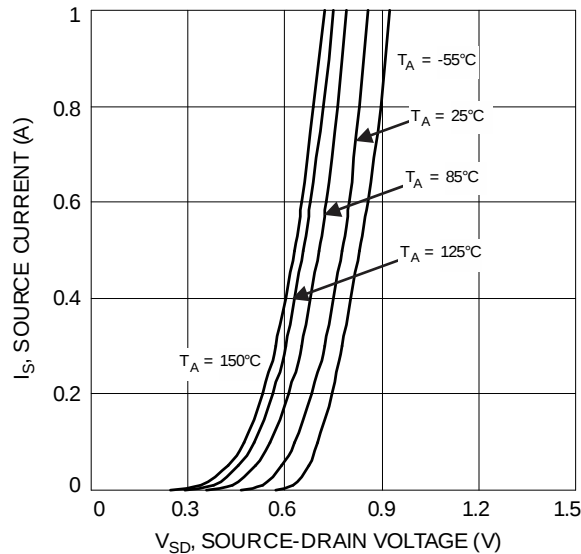


Figure 9 Diode Forward Voltage vs. Current

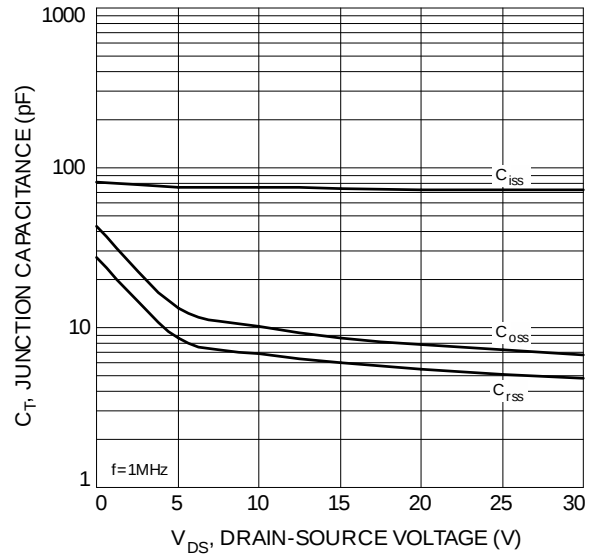


Figure 10 Typical Junction Capacitance

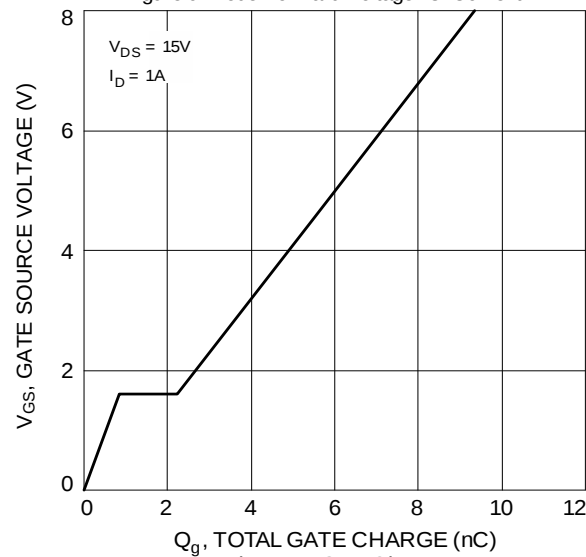


Figure 11 Gate Charge

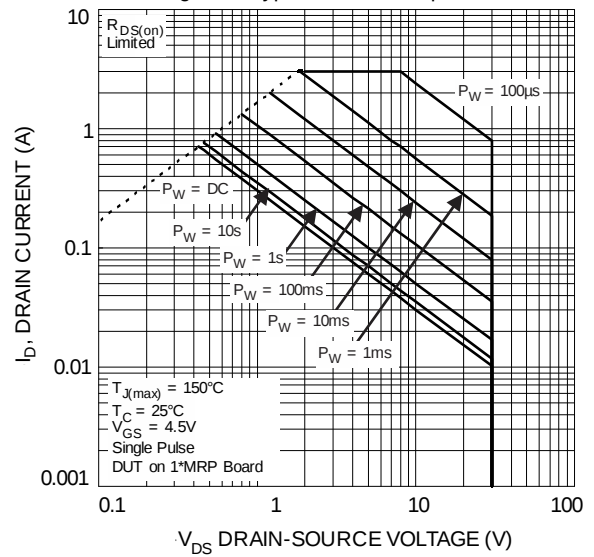
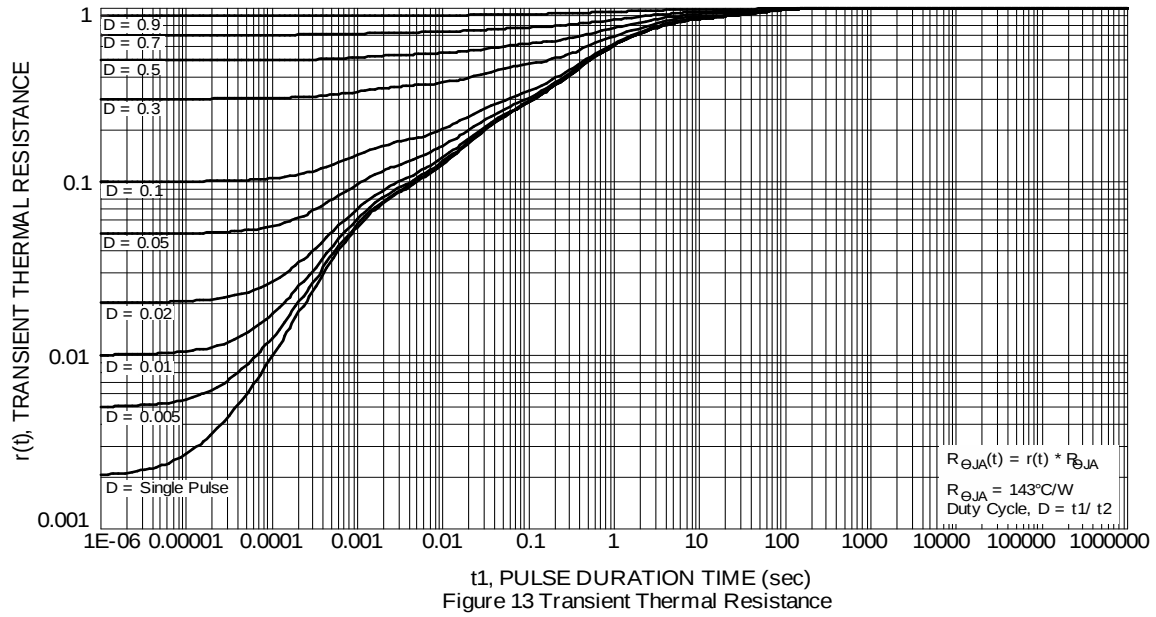


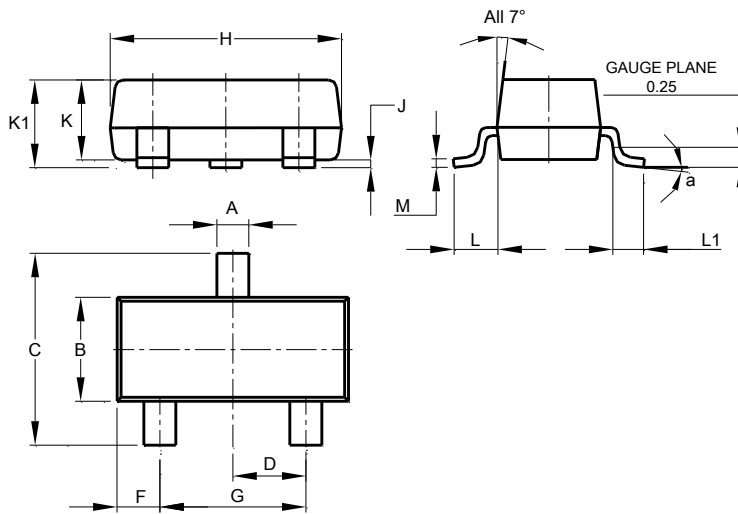
Figure # SOA, Safe Operation Area



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

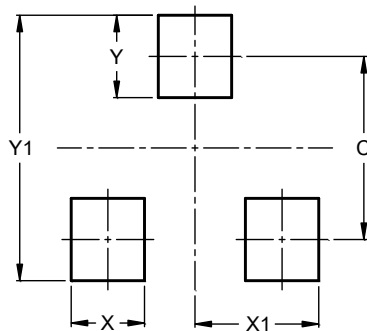


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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